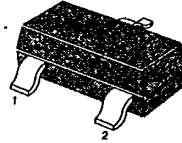


MMBT4124**NPN EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CE0}	25	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	200	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT3904 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C = 10μA, I _E = 0	30		V
*Collector-Emitter Breakdown Voltage	BV _{CE0}	I _C = 1.0mA, I _B = 0	25		V
Emitter-Base Breakdown Voltage	BV _{EB0}	I _E = 10μA, I _C = 0	5		V
Collector Cutoff Current	I _{CB0}	V _{CB} = 20V, I _E = 0		50	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 3V, I _C = 0		50	nA
*DC Current Gain	h _{FE}	V _{CE} = 1V, I _C = 2mA	120	360	
		V _{CE} = 1V, I _C = 50mA	60		
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 50mA, I _B = 5.0mA		0.3	V
*Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 50mA, I _B = 5.0mA		0.95	V
Current Gain-Bandwidth Product	f _T	I _C = 10mA, V _{CE} = 20V f = 100MHz	300		MHz
Output Capacitance	C _{ob}	V _{CB} = 5V, I _E = 0 f = 1.0MHz		4	pF
Noise Figure	NF	I _C = 100μA, V _{CE} = 5V R _S = 1KΩ f = 10Hz to 15.7KHz		5	dB

* Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Marking

